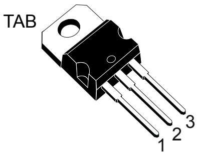
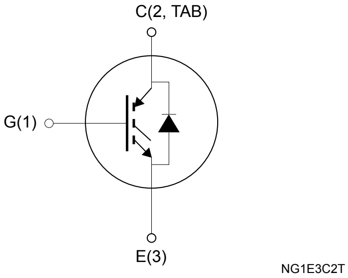
STGP20M65DF2

Datasheet

Trench gate field-stop, 650 V, 20 A, M series low-loss IGBT



TO-220



Features

- High short-circuit withstand time
- $V_{CE(sat)}$ = 1.55 V (typ.) @ I_C = 20 A
- Tight parameters distribution
- Safer paralleling
- Low thermal resistance
- Soft and very fast recovery antiparallel diode

Applications

- Motor control
- UPS
- PFC
- General-purpose inverters

Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the M series IGBTs, which represent an optimal balance between inverter system performance and efficiency where the low-loss and the short-circuit functionality is essential. Furthermore, the positive $V_{CE(sat)}$ temperature coefficient and the tight parameter distribution result in safer paralleling operation.

Product status link
STGP20M65DF2

Product summary	
Order code	STGP20M65DF2
Marking	G20M65DF2
Package	TO-220
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage (V_{GE} = 0)	650	V
I_C	Continuous collector current at T_C = 25 °C	40	A
	Continuous collector current at T_C = 100 °C	20	A
I_{CP}(1)	Pulsed collector current	80	A
V_{GE}	Gate-emitter voltage	±20	V
I_F	Continuous forward current at T_C = 25 °C	40	A
	Continuous forward current at T_C = 100 °C	20	A
I_{FP}(1)	Pulsed forward current	80	A
P_{TOT}	Total dissipation at T_C = 25 °C	166	W
T_{STG}	Storage temperature range	-55 to 150	°C
T_J	Operating junction temperature range	-55 to 175	°C

1. *Pulse width limited by maximum junction temperature.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case IGBT	0.9	°C/W
R_{thJC}	Thermal resistance junction-case diode	2.08	°C/W
R_{thJA}	Thermal resistance junction-ambient	62.5	°C/W

2 Electrical characteristics

T_C = 25 °C unless otherwise specified

Table 3. **Static characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	V_{GE} = 0 V, I_C = 250 µA	650			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE} = 15 V, I_C = 20 A		1.55	2.0	V
		V_{GE} = 15 V, I_C = 20 A, T_J = 125 °C		1.95		
		V_{GE} = 15 V, I_C = 20 A, T_J = 175 °C		2.1		
V_F	Forward on-voltage	I_F = 20 A		1.85		V
		I_F = 20 A, T_J = 125 °C		1.65		
		I_F = 20 A, T_J = 175 °C		1.55		
$V_{GE(th)}$	Gate threshold voltage	V_{CE} = V_{GE}, I_C = 500 µA	5	6	7	V
I_{CES}	Collector cut-off current	V_{GE} = 0 V, V_{CE} = 650 V			25	µA
I_{GES}	Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = ± 20 V			250	nA

Table 4. **Dynamic characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	V_{CE} = 25 V, f = 1 MHz, V_{GE} = 0 V	-	1688	-	pF
C_{oes}	Output capacitance		-	95	-	
C_{res}	Reverse transfer capacitance		-	35	-	
Q_g	Total gate charge	V_{CC} = 520 V, I_C = 20 A,	-	63	-	nC
Q_{ge}	Gate-emitter charge	V_{GE} = 0 to 15 V	-	15	-	
Q_{gc}	Gate-collector charge	(see Figure 29. Gate charge test circuit)	-	26	-	

Table 5. IGBT switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{CE} = 400 V, I_C = 20 A, V_{GE} = 15 V, R_G = 12 Ω (see Figure 28. Test circuit for inductive load switching)		26	-	ns
t_r	Current rise time			10.8	-	ns
$(di/dt)_{on}$	Turn-on current slope			1409	-	A/μs
$t_{d(off)}$	Turn-off delay time			108	-	ns
t_f	Current fall time			65	-	ns
E_{on} (1)	Turn-on switching energy			0.14	-	mJ
E_{off} (2)	Turn-off switching energy			0.56	-	mJ
E_{ts}	Total switching energy			0.7	-	mJ
$t_{d(on)}$	Turn-on delay time	V_{CE} = 400 V, I_C = 20 A, V_{GE} = 15 V, R_G = 12 Ω, T_J = 175 °C (see Figure 28. Test circuit for inductive load switching)		28.4	-	ns
t_r	Current rise time			11.2	-	ns
$(di/dt)_{on}$	Turn-on current slope			1393	-	A/μs
$t_{d(off)}$	Turn-off delay time			107	-	ns
t_f	Current fall time			145	-	ns
E_{on} (1)	Turn-on switching energy			0.3	-	mJ
E_{off} (2)	Turn-off switching energy			0.85	-	mJ
E_{ts}	Total switching energy			1.15	-	mJ
t_{sc}	Short-circuit withstand time	V_{CC} = 400 V, V_{GE} = 13 V, T_{Jstart} = 150 °C	10		-	μs
		V_{CC} = 400 V, V_{GE} = 15 V, T_{Jstart} = 150 °C	6		-	

1. *Including the reverse recovery of the diode.*
2. *Including the tail of the collector current.*

Table 6. Diode switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	I_F = 20 A, V_R = 400 V, V_{GE} = 15 V, di/dt = 1000 A/μs (see Figure 28. Test circuit for inductive load switching)	-	166		ns
Q_{rr}	Reverse recovery charge		-	690		nC
I_{rrm}	Reverse recovery current		-	13.2		A
dI_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	769		A/μs
E_{rr}	Reverse recovery energy		-	81		μJ
t_{rr}	Reverse recovery time	I_F = 20 A, V_R = 400 V, V_{GE} = 15 V, T_J = 175 °C, di/dt = 1000 A/μs (see Figure 28. Test circuit for inductive load switching)	-	281		ns
Q_{rr}	Reverse recovery charge		-	2010		nC
I_{rrm}	Reverse recovery current		-	19.6		A
dI_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	370		A/μs
E_{rr}	Reverse recovery energy		-	215		μJ

2.1 Electrical characteristics (curves)

Figure 1. Power dissipation vs case temperature

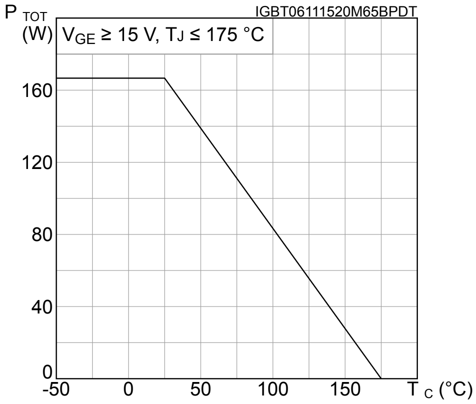


Figure 2. Collector current vs case temperature

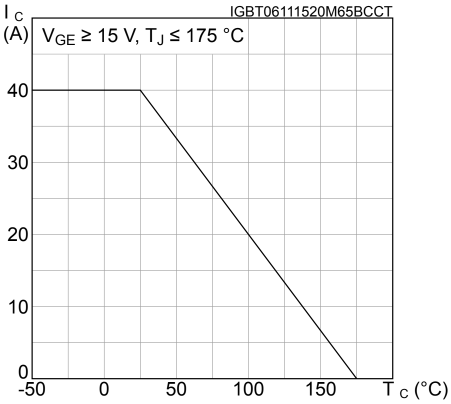


Figure 3. Output characteristics (T_J = 25 °C)

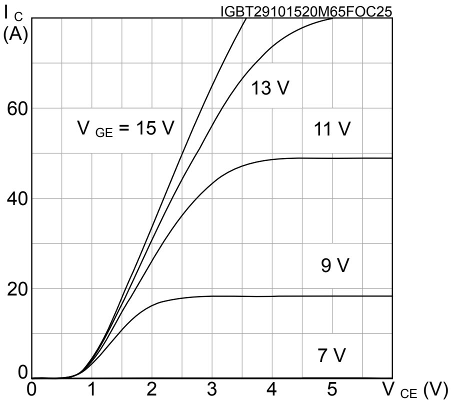


Figure 4. Output characteristics (T_J = 175 °C)

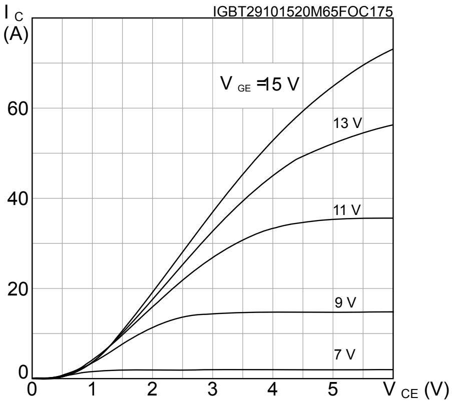


Figure 5. V_{CE}(sat) vs junction temperature

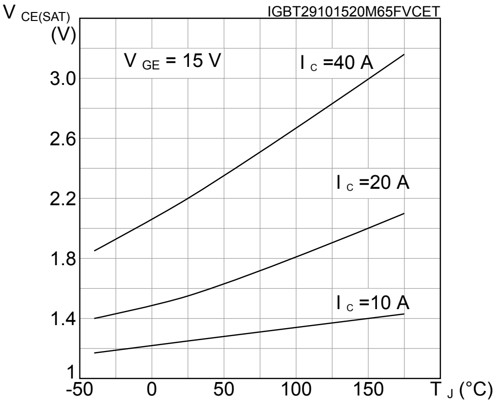


Figure 6. V_{CE}(sat) vs collector current

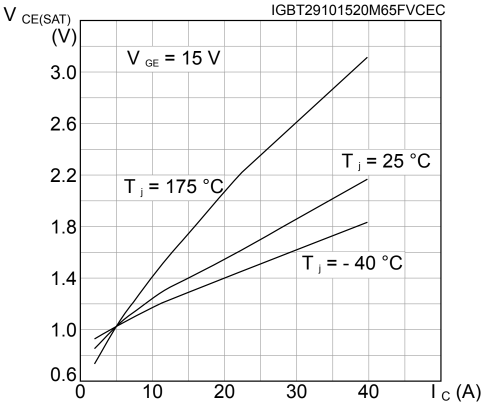


Figure 7. **Collector current vs switching frequency**

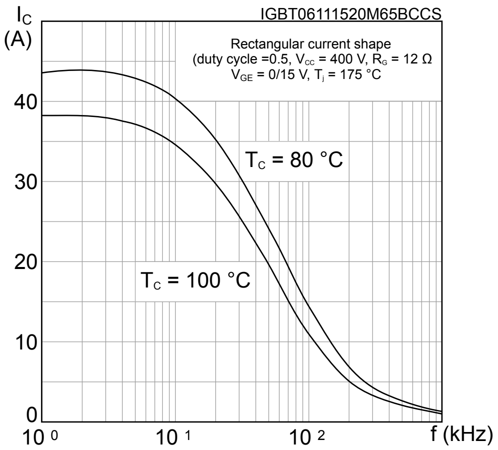


Figure 8. **Forward bias safe operating area**

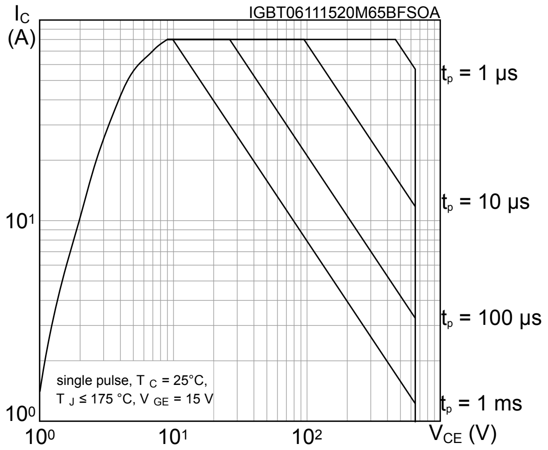


Figure 9. **Transfer characteristics**

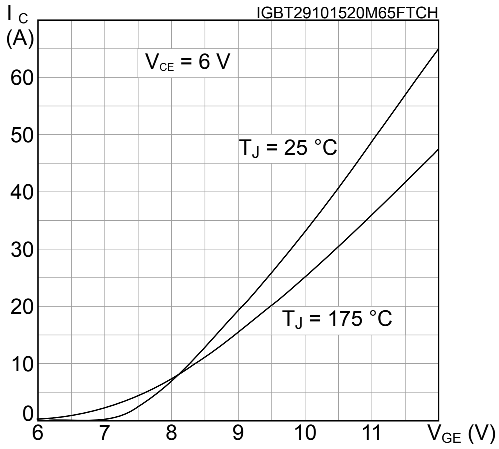


Figure 10. **Diode V_F vs forward current**

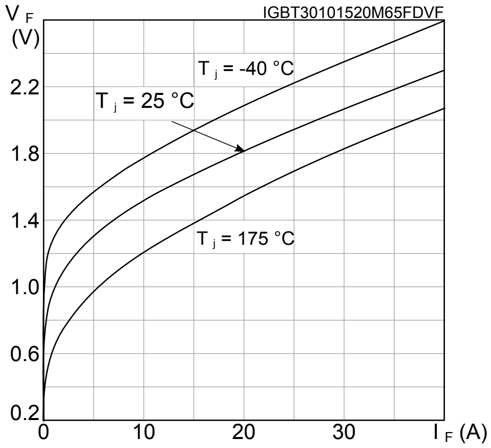


Figure 11. **Normalized $V_{GE(th)}$ vs junction temperature**

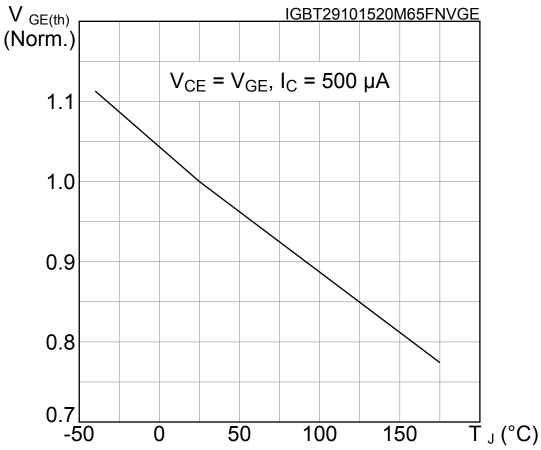


Figure 12. **Normalized $V_{(BR)CES}$ vs junction temperature**

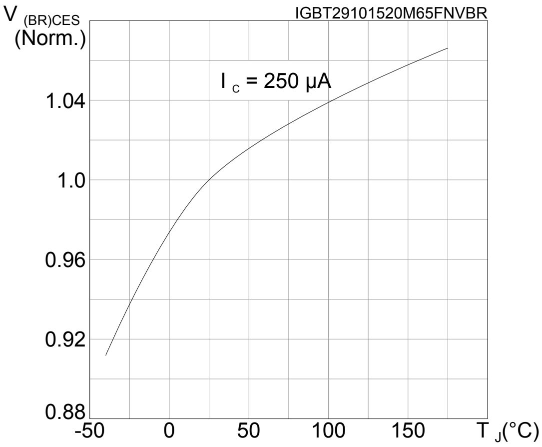


Figure 13. Capacitance variations

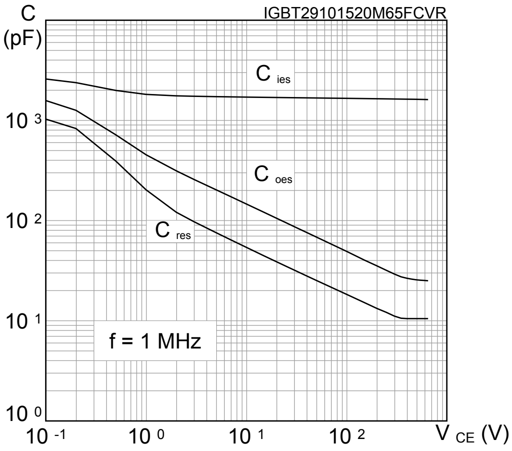


Figure 14. Gate charge vs gate-emitter voltage

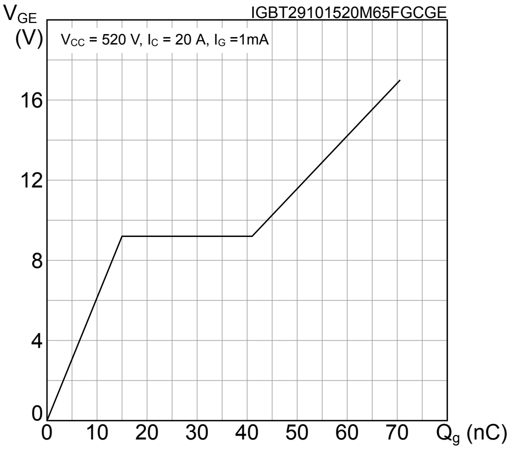


Figure 15. Switching energy vs collector current

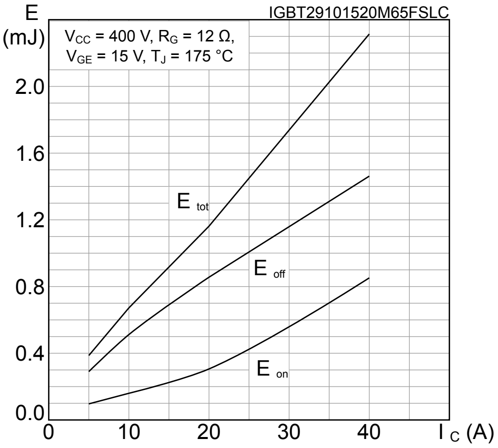


Figure 16. Switching energy vs gate resistance

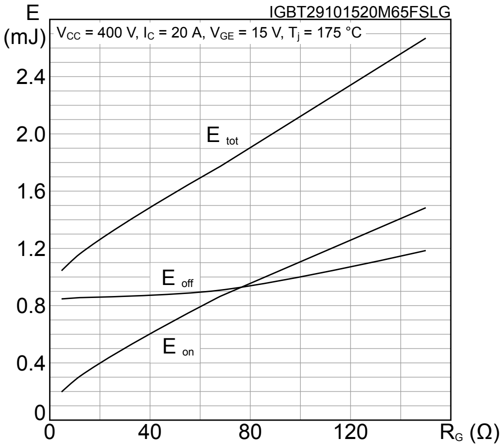


Figure 17. Switching energy vs temperature

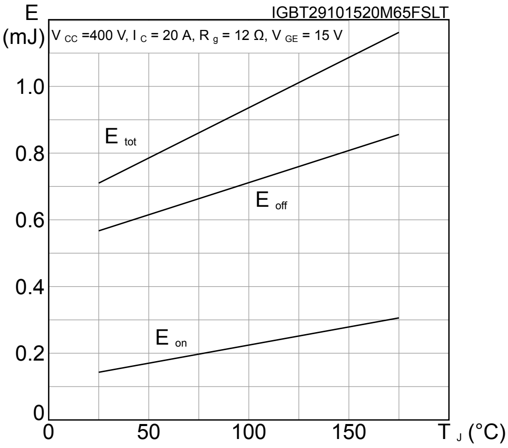


Figure 18. Switching energy vs collector emitter voltage

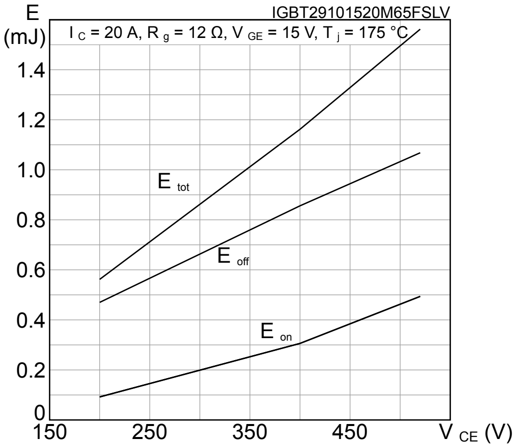


Figure 19. Short-circuit time and current vs V_{GE}

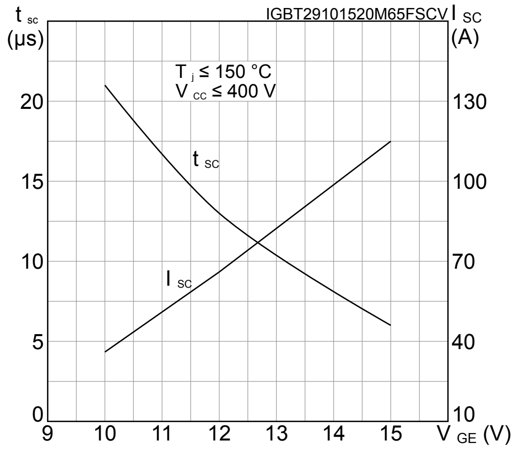


Figure 20. Switching times vs collector current

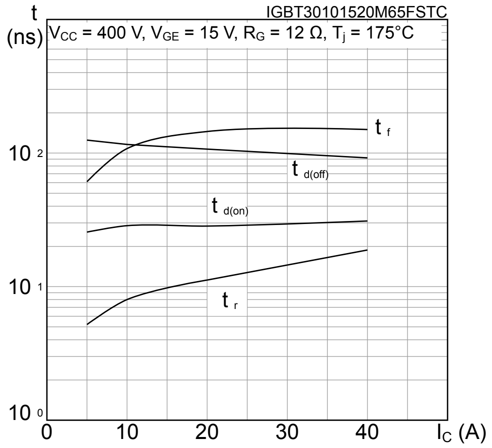


Figure 21. Switching times vs gate resistance

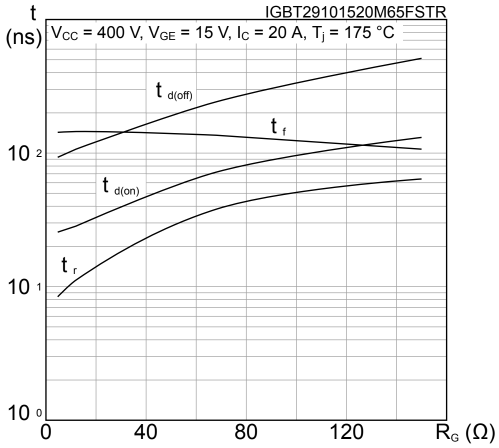


Figure 22. Reverse recovery current vs diode current slope

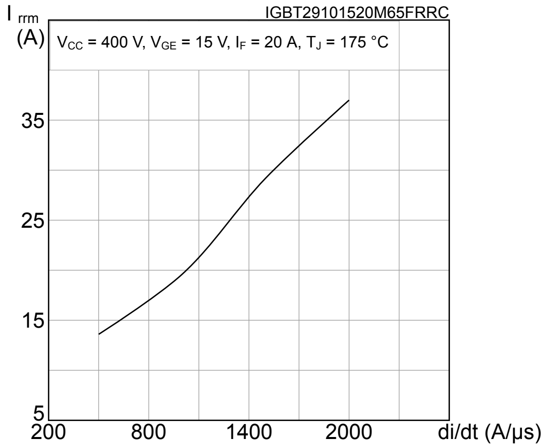


Figure 23. Reverse recovery time vs diode current slope

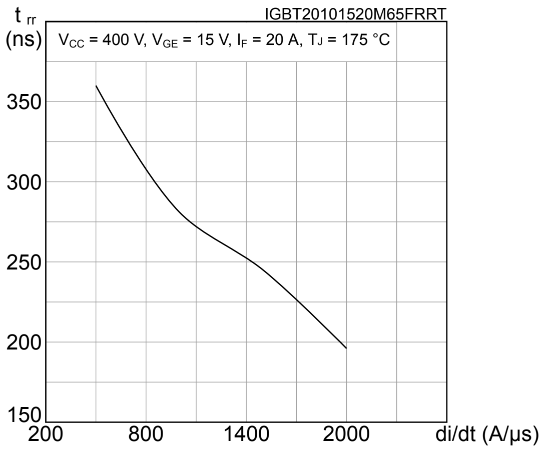


Figure 24. Reverse recovery charge vs diode current slope

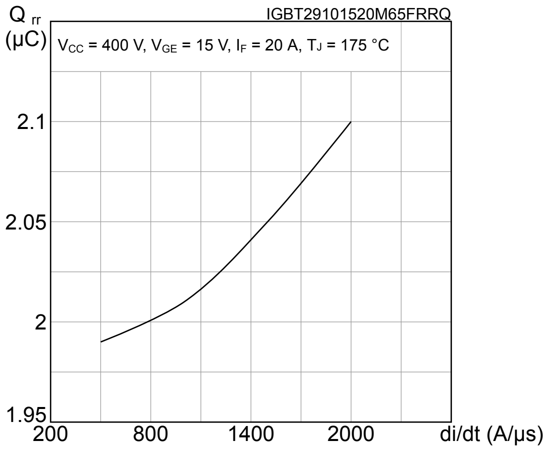


Figure 25. Reverse recovery energy vs diode current slope

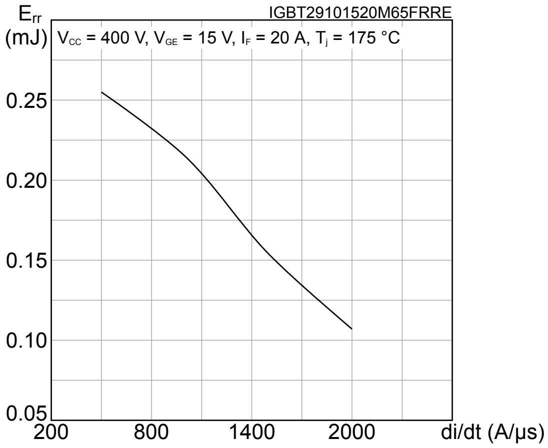


Figure 26. Thermal impedance for IGBT

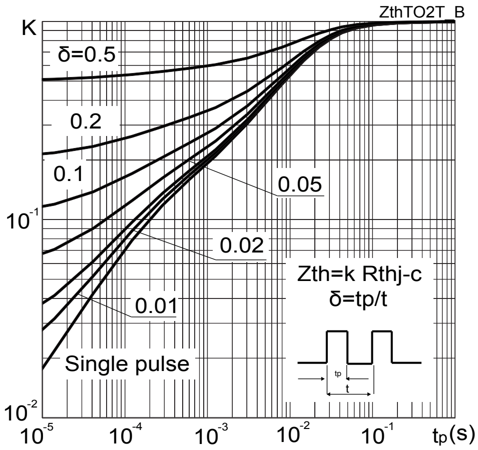
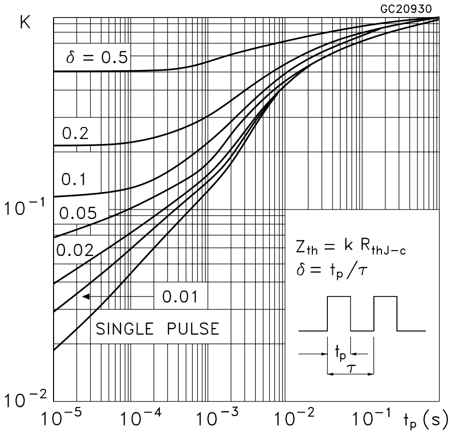


Figure 27. Thermal impedance for diode



3 Test circuits

Figure 28. Test circuit for inductive load switching

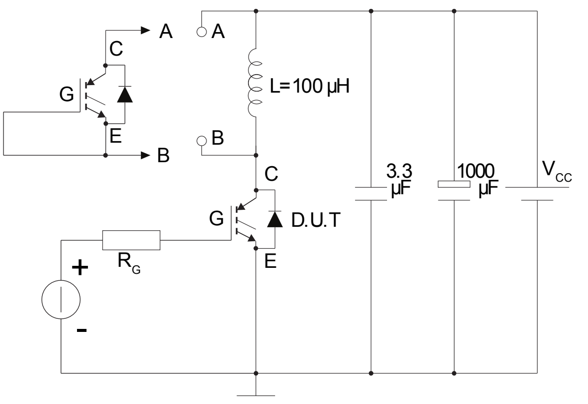


Figure 29. Gate charge test circuit

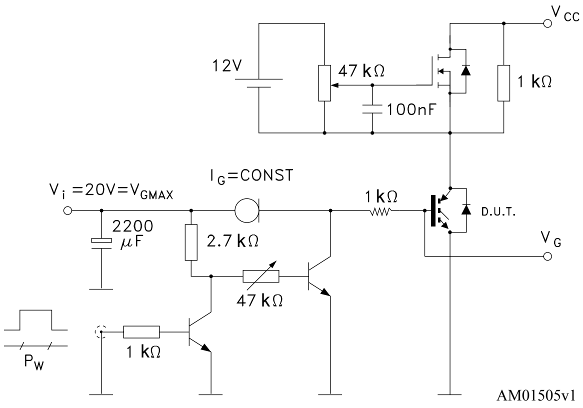


Figure 30. Switching waveform

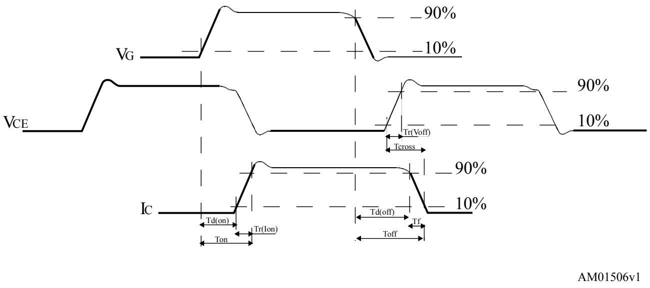
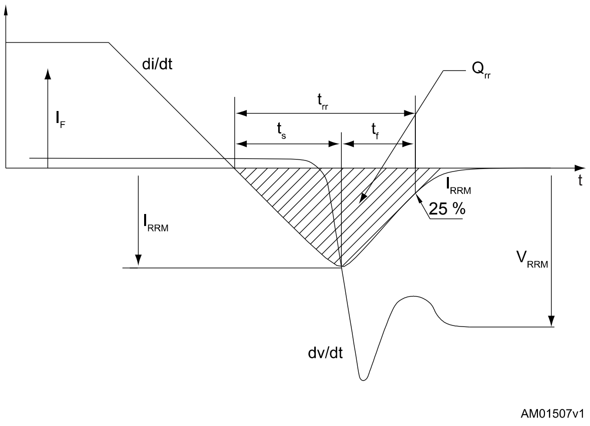


Figure 31. Diode reverse recovery waveform

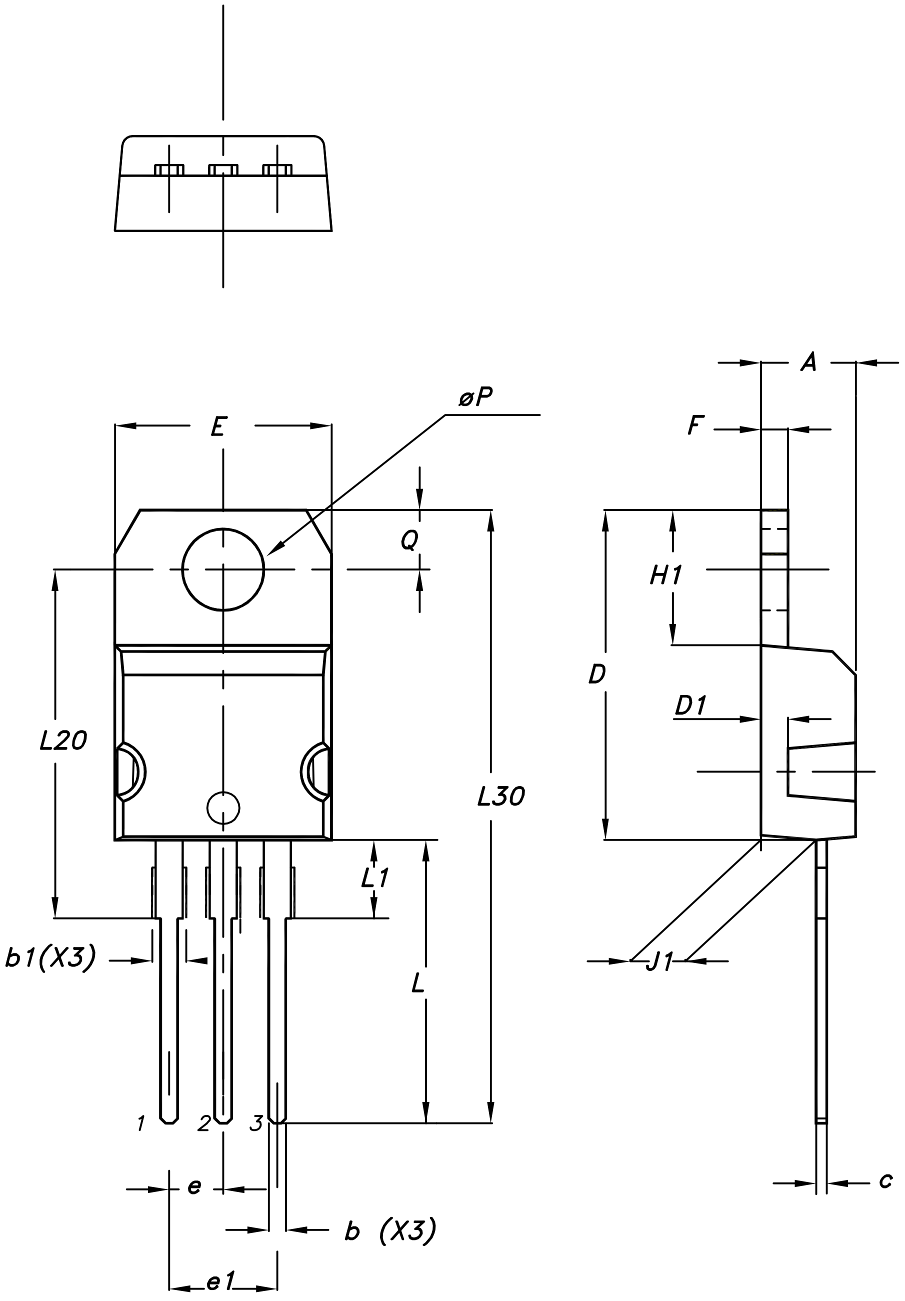


4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 TO-220 type A package information

Figure 32. TO-220 type A package outline



0015988_typeA_Rev_21

Table 7. TO-220 type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

Revision history

Table 8. **Document revision history**

Date	Revision	Changes
11-Nov-2015	1	First release.
18-Apr-2016	2	Updated *Figure 13: "Normalized* $V_{(BR)CES}$ *vs. junction temperature ".*
08-Oct-2018	3	Updated Table 3. Static characteristics. Minor text changes

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